GaNPower International Inc.

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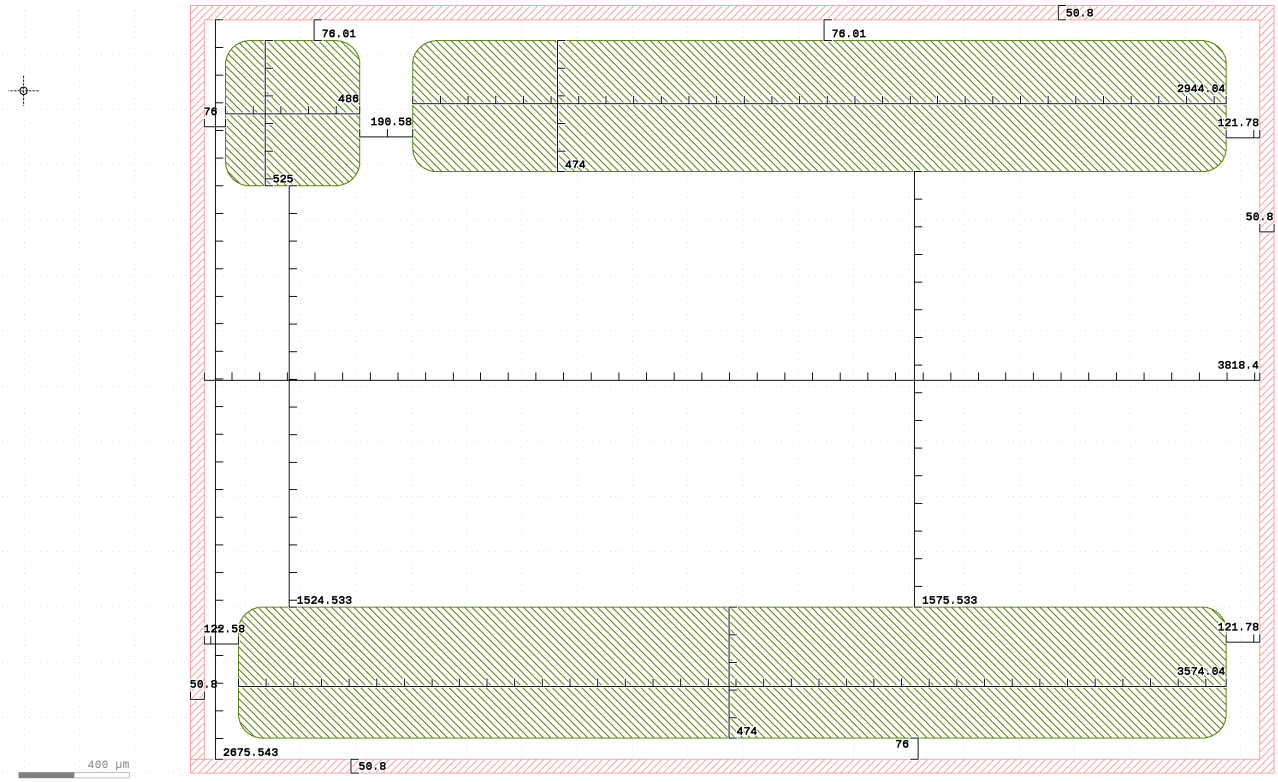
230 -3410 LOUGHEED HWY
VANCOUVER, BC, V5M 2A4 CANADA

Cu-Hollyburn30

N-channel 1200V 30A GaNPower HEMT

Die Appearance:



Specifications:

Wafer Diameter	6 inches
Nominal Back Metal composition, thickness	None
Nominal Front Metal composition, thickness	Cu, 14 µm
Die Dimensions (not including sawing streets)	2777.14 µm × 3920.0 µm
Gate pad size	525 µm × 486 µm
Wafer Thickness	1000 µm
Street Width	80 µm
Recommended Storage Environment	Desiccated N_2 environment, without contamination

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Wire bonding:

Al and Cu wires are applicable.

Device Characteristics:

Parameters		Conditions	Min	Typical	Max	
$I_{DS\text{-}max}$	Drain to source current	V_{GS}=6V, T_c=25 °C		30		A
$V_{DS\text{-}max}$	Drain-Source breakdown voltage	V_{GS}=0V, I_D< 20μA, T_J=25 °C		1200		V
$V_{GS(TH)}$	Gate threshold voltage	V_{DS}=V_{GS}, I_d=20mA (T_J=25 °C)		1.2	2.0	V
I_{DSS}	Zero gate voltage drain leakage current	V_{GS}=0V, V_{DS}= 1200V T_J = 25 °C		2.5	50	μA
I_{GSS}	Gate-Source Leakage	V_{GS} = 6V, V_{DS} = 0V		0.3	3	mA
R_{DSON}	drain-source on resistance	V_{GS}=6V, I_D=6A T_J = 25 °C		55	70	mΩ

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Revision History

Date	Version No.	Modifications
2025.03.28	1.0	Preliminary datasheet